

RJK5026DPP

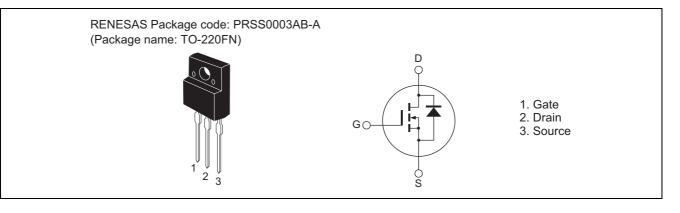
Silicon N Channel MOS FET High Speed Power Switching

> REJ03G1734-0100 Rev.1.00 Sep 11, 2008

Features

- Low on-resistance
- Low leakage current
- High speed switching

Outline



Absolute Maximum Ratings

 $(Ta = 25^{\circ}C)$

Item	Symbol	Ratings	Unit
Drain to source voltage	V _{DSS}	500	V
Gate to source voltage	V _{GSS}	±30	V
Drain current	ID ^{Note4}	6	А
Drain peak current	I _{D (pulse)} Note1	18	А
Body-drain diode reverse drain current	I _{DR}	6	А
Body-drain diode reverse drain peak current	Note1 I _{DR (pulse)}	18	А
Avalanche current	I _{AP} ^{Note3}	4	А
Avalanche energy	E _{AR} ^{Note3}	0.88	mJ
Channel dissipation	Pch ^{Note2}	28.5	W
Channel to case thermal impedance	θch-c	4.38	°C/W
Channel temperature	Tch	150	°C
Storage temperature	Tstg	-55 to +150	°C

Notes: 1. PW \leq 10 $\mu s,$ duty cycle \leq 1%

2. Value at Tc = 25°C

3. STch = 25° C, Tch $\leq 150^{\circ}$ C

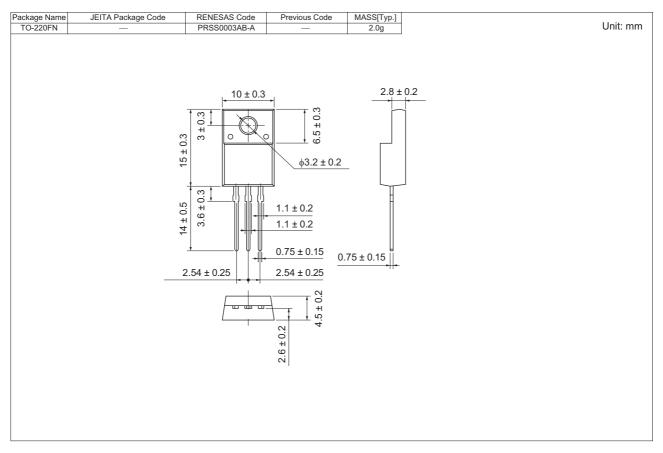
4. Limited by maximum safe operation area

Electrical Characteristics

						$(Ta = 25^{\circ}C)$
Item	Symbol	Min	Тур	Мах	Unit	Test conditions
Drain to source breakdown voltage	V _{(BR)DSS}	500	_	_	V	$I_D = 10 \text{ mA}, V_{GS} = 0$
Zero gate voltage drain current	I _{DSS}	_		1	μΑ	$V_{DS} = 500 \text{ V}, \text{ V}_{GS} = 0$
Gate to source leak current	I _{GSS}	_	_	±0.1	μΑ	$V_{GS} = \pm 30$ V, $V_{DS} = 0$
Gate to source cutoff voltage	V _{GS(off)}	3.0	_	4.5	V	$V_{DS} = 10 \text{ V}, I_{D} = 1 \text{ mA}$
Static drain to source on state resistance	$R_{\text{DS(on)}}$		1.35	1.70	Ω	$I_D = 3 \text{ A}, V_{GS} = 10 \text{ V}^{Note5}$
Input capacitance	Ciss		440		pF	$V_{DS} = 25 V$ $V_{GS} = 0$ $f = 1 MHz$
Output capacitance	Coss		52		pF	
Reverse transfer capacitance	Crss	_	7	—	pF	
Turn-on delay time	t _{d(on)}	_	26	—	ns	$I_{D} = 3 A V_{GS} = 10 V R_{L} = 83.3 \Omega Rg = 10 \Omega$
Rise time	tr	_	19	_	ns	
Turn-off delay time	t _{d(off)}	_	50	—	ns	
Fall time	t _f	-	14	—	ns	
Total gate charge	Qg	-	14	—	nC	$V_{DD} = 400 V$ $V_{GS} = 10 V$ $I_D = 6 A$
Gate to source charge	Qgs		2.5	—	nC	
Gate to drain charge	Qgd	—	6.9	—	nC	
Body-drain diode forward voltage	V _{DF}	—	0.9	1.5	V	$I_F = 6 A, V_{GS} = 0^{Note5}$
Body-drain diode reverse recovery time	t _{rr}		230		ns	$I_F = 6 \text{ A}, V_{GS} = 0$ $di_F/dt = 100 \text{ A}/\mu\text{s}$

Notes: 5. Pulse test

Package Dimensions



Ordering Information

Part No.	Quantity	Shipping Container
RJK5026DPP-00-T2	1050 pcs	Box (Tube)

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